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TOSHIBA WELDED EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK3074

RF POWER MOSFET FOR VHF-AND UHF-BAND POWER AMPLIFIER

(Note)The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment. These TOSHIBA products are neither intended nor warranted for any other use. Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.

- Output Power : $P_O \geq 630\text{mW}$
- Power Gain : $G_P \geq 14.9\text{dB}$
- Drain Efficiency : $\eta_D \geq 45\%$

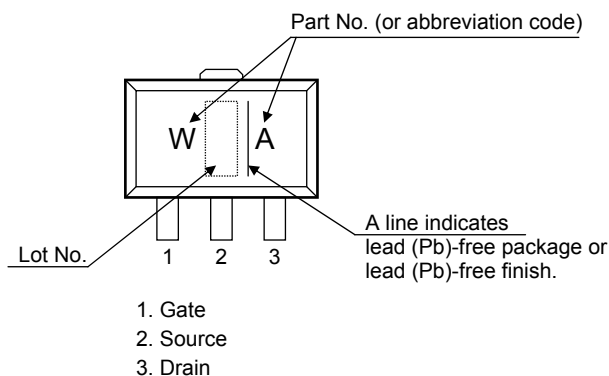
ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	25	V
Drain Current	I_D	1	A
Drain Power Dissipation	P_D (Note 1)	3	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-45 \sim 150$	$^\circ\text{C}$

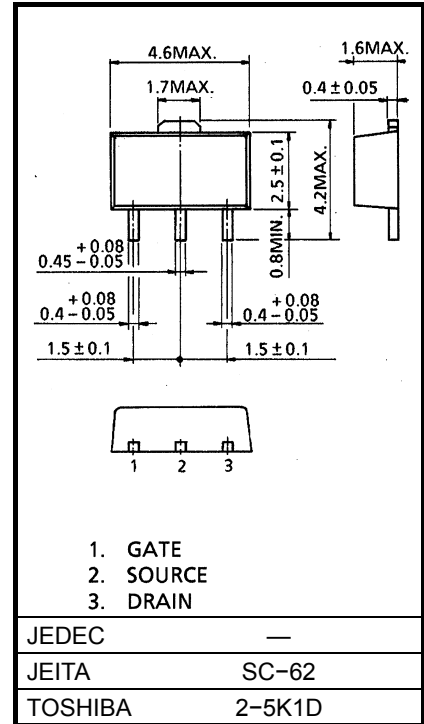
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: $T_c = 25^\circ\text{C}$ When mounted on a 1.6mm glass epoxy PCB

MARKING



Unit in mm



Weight: 0.05 g (typ.)

Caution: This device is sensitive to electrostatic discharge.

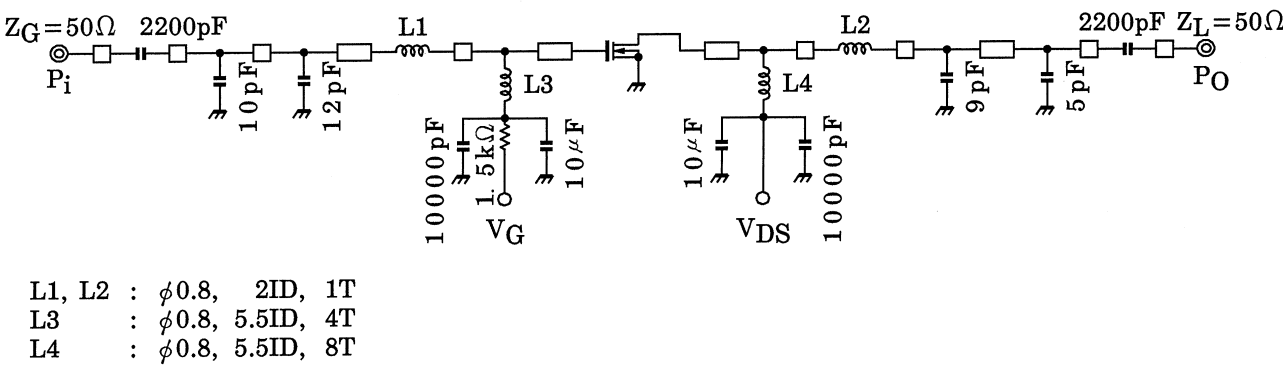
Please make enough tool and equipment earthed when you handle.

2SK3074 07"供应商
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

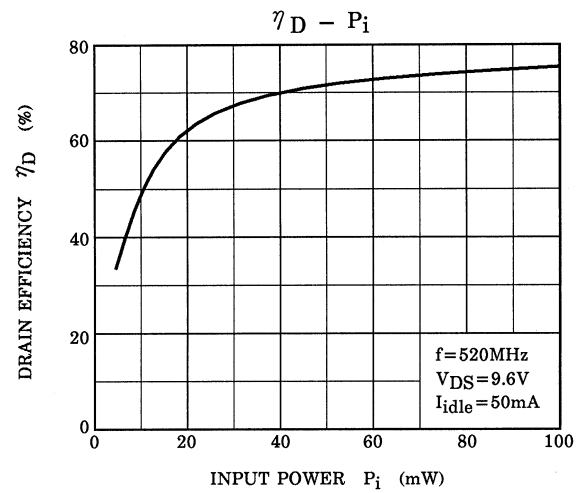
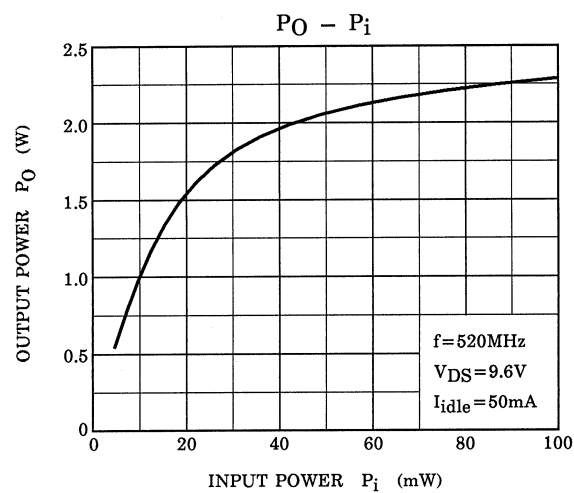
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P _O	V _{DS} = 9.6V I _{idle} = 50mA (V _{GS} = adjust) f = 520MHz, P _i = 20mW	630	—	—	mW
Drain Efficiency	η _D		45	—	—	%
Power Gain	G _p		14.9	—	—	dB
Gate Threshold Voltage	V _{th}	V _{DS} = 9.6V, I _D = 0.5mA	1.4	1.9	2.4	V
Drain Cut-off Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0	—	—	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 10V, V _{DS} = 0	—	—	5	μA

Note 2: These characteristic values are measured using measurement tools specified by Toshiba.

RF OUTPUT POWER TEST FIXTURE



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Note 3: These are only typical curves and devices are not necessarily guaranteed at these curves.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
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